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Kind regards,

Team Nexperia

0.5 A very low V_F MEGA Schottky barrier rectifiers

Rev. 02 — 13 January 2010

Produ

Product data sheet

1. **Product profile**

1.1 General description

Planar Maximum Efficiency General Application (MEGA) Schottky barrier rectifier with an integrated guard ring for stress protection encapsulated in small SMD package.

Table 1. **Product overview**

Type number	Package		Configuration
	NXP	JEITA	
PMEG2005EH	SOD123F	-	single diode
PMEG3005EH			
PMEG4005EH			
PMEG2005EJ	SOD323F	SC-90	single diode
PMEG3005EJ			
PMEG4005EJ			

1.2 Features

- Forward current: 0.5 A
- Very low forward voltage
- Flat lead SMD package

1.3 Applications

- Low voltage rectification
- High efficiency DC-to-DC conversion
- Switch mode power supply
- Inverse polarity protection
- Low power consumption applications



1.4 Quick reference data

Table 2. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
l _F	forward current	$T_{sp} \le 55 ^{\circ}C$	-	-	0.5	Α
V_R	reverse voltage					
	PMEG2005EH, PMEG2005EJ		-	-	20	V
	PMEG3005EH, PMEG3005EJ		-	-	30	V
	PMEG4005EH, PMEG4005EJ		-	-	40	V
V_{F}	forward voltage	$I_F = 500 \text{ mA}$	<u>[1]</u>			
	PMEG2005EH, PMEG2005EJ		-	355	390	mV
	PMEG3005EH, PMEG3005EJ		-	380	430	mV
	PMEG4005EH, PMEG4005EJ		-	420	470	mV

^[1] Pulse test: $t_p \le 300~\mu s;~\delta \le 0.02.$

2. Pinning information

Table 3. Pinning

· ····································		
Description	Simplified outline	Symbol
cathode	[1]	. 84
anode	1 2	1 1 2
		sym001
	cathode	cathode [1]

^[1] The marking bar indicates the cathode.

3. Ordering information

Table 4. Ordering information

Type number	Package					
	Name	Description	Version			
PMEG2005EH	-	plastic surface mounted package; 2 leads	SOD123F			
PMEG3005EH						
PMEG4005EH						
PMEG2005EJ	SC-90	plastic surface mounted package; 2 leads	SOD323F			
PMEG3005EJ						
PMEG4005EJ	_					

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4. Marking

Table 5. Marking codes

Type number	Marking code
PMEG2005EH	A3
PMEG3005EH	A4
PMEG4005EH	A5
PMEG2005EJ	CC
PMEG3005EJ	CD
PMEG4005EJ	CE

5. Limiting values

Table 6. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_R	reverse voltage				
	PMEG2005EH, PMEG2005EJ		-	20	V
	PMEG3005EH, PMEG3005EJ		-	30	V
	PMEG4005EH, PMEG4005EJ		-	40	V
l _F	forward current	T _{sp} ≤ 55 °C	-	0.5	Α
I _{FRM}	repetitive peak forward current	$t_p \leq 1 \text{ ms; } \delta \leq 0.25$	-	7	Α
I _{FSM}	non-repetitive peak forward current	t = 8 ms square wave	-	10	Α
P _{tot}	total power dissipation	$T_{amb} \le 25 ^{\circ}C$			
	SOD123F		[1] -	375	mW
			[2] _	830	mW
	SOD323F		<u>[1]</u> -	360	mW
			[2] _	830	mW
Tj	junction temperature		-	150	°C
T _{amb}	ambient temperature		-65	+150	°C
T _{stg}	storage temperature		-65	+150	°C

^[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

^[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for cathode 1 cm².

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6. Thermal characteristics

Table 7. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	[1][2]				
	SOD123F			-	-	330	K/W
	SOD323F			-	-	350	K/W
			[1][3]	-	-	150	K/W
$R_{th(j-sp)}$	thermal resistance from junction to solder point						
	SOD123F			-	-	60	K/W
	SOD323F			-	-	55	K/W

^[1] Schottky barrier diodes thermal run-away has to be considered, as in some applications the reverse power losses P_R are a significant part of the total power losses. Nomograms for determining the reverse power losses P_R and I_{F(AV)} rating will be available on request.

^[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

^[3] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for cathode 1 cm².

7. Characteristics

Table 8. Characteristics

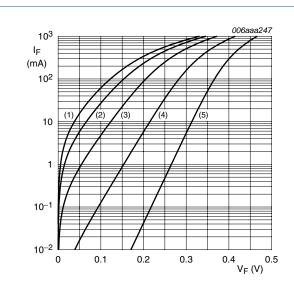
T_{amb} = 25 °C unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
/ _F	forward voltage		<u>[1]</u>			
	PMEG2005EH,	$I_F = 0.1 \text{ mA}$	-	90	130	mV
	PMEG2005EJ	$I_F = 1 \text{ mA}$	-	150	190	mV
		$I_F = 10 \text{ mA}$	-	210	240	mV
		$I_F = 100 \text{ mA}$	-	280	330	mV
		$I_F = 500 \text{ mA}$	-	355	390	mV
	PMEG3005EH,	$I_F = 0.1 \text{ mA}$	-	90	130	mV
	PMEG3005EJ	$I_F = 1 \text{ mA}$	-	150	200	mV
		$I_F = 10 \text{ mA}$	-	215	250	mV
		$I_F = 100 \text{ mA}$	-	285	340	mV
		$I_F = 500 \text{ mA}$	-	380	430	mV
	PMEG4005EH, PMEG4005EJ	$I_F = 0.1 \text{ mA}$	-	95	130	mV
		$I_F = 1 \text{ mA}$	-	155	210	mV
		$I_F = 10 \text{ mA}$	-	220	270	mV
		$I_F = 100 \text{ mA}$	-	295	350	mV
		$I_F = 500 \text{ mA}$	-	420	470	mV
R	reverse current		[1][2]			
	PMEG2005EH, PMEG2005EJ	V _R = 10 V	-	15	40	μΑ
		V _R = 20 V	-	40	200	μΑ
	PMEG3005EH,	V _R = 10 V	-	12	30	μΑ
	PMEG3005EJ	$V_R = 30 \text{ V}$	-	40	150	μΑ
	PMEG4005EH,	V _R = 10 V	-	7	20	μΑ
	PMEG4005EJ	$V_R = 40 \text{ V}$	-	30	100	μΑ
C _d	diode capacitance	$V_R = 1 V$; $f = 1 MHz$				
	PMEG2005EH, PMEG2005EJ		-	66	80	pF
	PMEG3005EH, PMEG3005EJ		-	55	70	pF
	PMEG4005EH, PMEG4005EJ		-	43	50	pF

^[1] Pulse test: $t_p \leq 300~\mu s;~\delta \leq 0.02.$

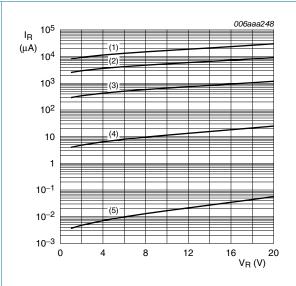
^[2] Schottky barrier rectifier thermal run-away has to be considered, as in some applications the reverse power losses P_R are a significant part of the total power losses. Nomograms for determining the reverse power losses P_R and I_{F(AV)} rating will be available on request.

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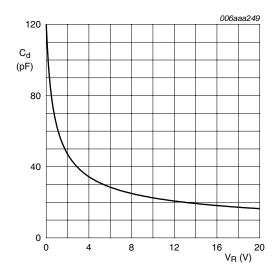
- (1) $T_{amb} = 150 \, ^{\circ}C$
- (2) $T_{amb} = 125 \, ^{\circ}C$
- (3) $T_{amb} = 85 \, ^{\circ}C$
- (4) $T_{amb} = 25 \, ^{\circ}C$
- (5) $T_{amb} = -40 \, ^{\circ}C$





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- (3) $T_{amb} = 85 \, ^{\circ}C$
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- (5) $T_{amb} = -40 \, ^{\circ}C$

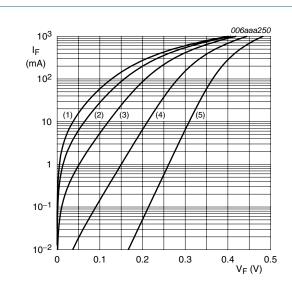
Fig 2. PMEG2005EH, PMEG2005EJ: Reverse current as a function of reverse voltage; typical values



 $T_{amb} = 25 \, ^{\circ}C; f = 1 \, MHz$

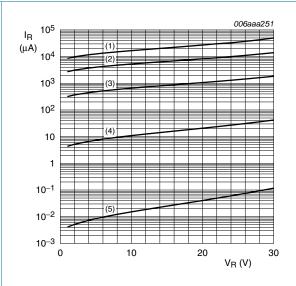
Fig 3. PMEG2005EH, PMEG2005EJ: Diode capacitance as a function of reverse voltage; typical values

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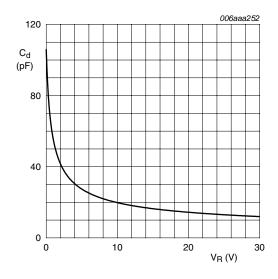
- (1) $T_{amb} = 150 \, ^{\circ}C$
- (2) $T_{amb} = 125 \, ^{\circ}C$
- (3) $T_{amb} = 85 \, ^{\circ}C$
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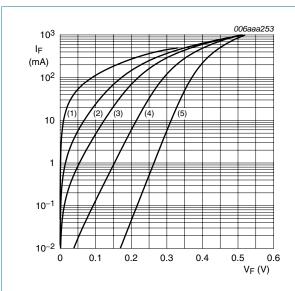
Fig 5. PMEG3005EH, PMEG3005EJ: Reverse current as a function of reverse voltage; typical values



 $T_{amb} = 25 \, ^{\circ}C; f = 1 \, MHz$

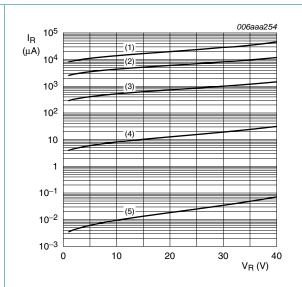
Fig 6. PMEG3005EH, PMEG3005EJ: Diode capacitance as a function of reverse voltage; typical values

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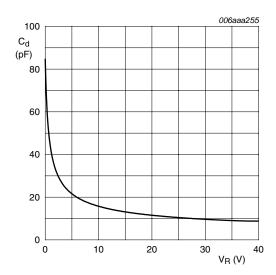
- (1) $T_{amb} = 150 \, ^{\circ}C$
- (2) $T_{amb} = 125 \, ^{\circ}C$
- (3) $T_{amb} = 85 \, ^{\circ}C$
- (4) $T_{amb} = 25 \, ^{\circ}C$
- (5) $T_{amb} = -40 \, ^{\circ}C$





- (1) $T_{amb} = 150 \, ^{\circ}C$
- (2) $T_{amb} = 125 \, ^{\circ}C$
- (3) $T_{amb} = 85 \, ^{\circ}C$
- (4) $T_{amb} = 25 \, ^{\circ}C$
- (5) $T_{amb} = -40 \, ^{\circ}C$

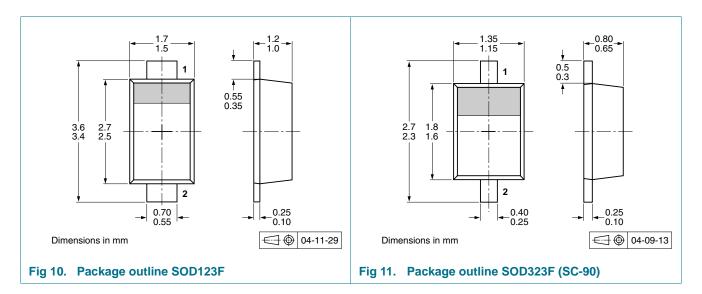
Fig 8. PMEG4005EH, PMEG4005EJ: Reverse current as a function of reverse voltage; typical values



 $T_{amb} = 25 \, ^{\circ}C; f = 1 \, MHz$

Fig 9. PMEG4005EH, PMEG4005EJ: Diode capacitance as a function of reverse voltage; typical values

8. Package outline



9. Packing information

Table 9. Packing methods

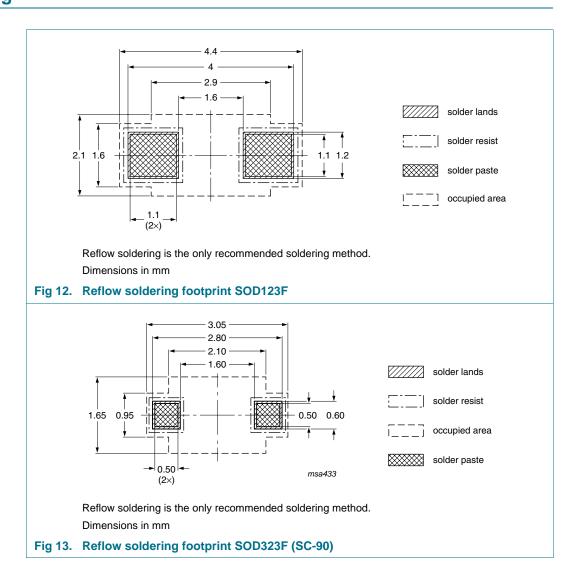
The indicated -xxx are the last three digits of the 12NC ordering code.[1]

Type number	Package	Description	Packing quantity		
			3000	10000	
PMEG2005EH	SOD123F	4 mm pitch, 8 mm tape and reel	-115	-135	
PMEG3005EH					
PMEG4005EH					
PMEG2005EJ	SOD323F	4 mm pitch, 8 mm tape and reel	-115	-135	
PMEG3005EJ					
PMEG4005EJ					

[1] For further information and the availability of packing methods, see $\underline{\text{Section 13}}$.

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10. Soldering



0.5 A very low V_F MEGA Schottky barrier rectifiers

11. Revision history

Table 10. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PMEGXX05EH_EJ_SER_2	20100113	Product data sheet	-	PMEGXX05EH_EJ_SER_1
Modifications:		9		name NXP Semiconductors, es were made to the technical
PMEGXX05EH_EJ_SER_1	20050412	Product data sheet	-	-

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12. Legal information

12.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
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NSR05F40QNXT5G NSVR05F40NXT5G JANS1N6640 SB07-03C-TB-H SB1003M3-TL-W SBAT54CWT1G SK32A-LTP SK33A-TP SK34A
TP SK34B-TP SMD1150PL-TP SMD1200PL-TP ACDBN160-HF SS3003CH-TL-E STPS3045CPIRG STPS30S45CW PDS3100Q-7

GA01SHT18 CRS10I30A(TE85L,QM CRS10I30B(TE85L,QM MBR1240MFST1G MBR20100CT-BP MBRB30H30CT-1G BAS28E6433HTMA1

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